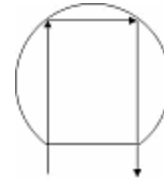


Part Number		Customer		icemos tech ltd	
Category	Parameter	Specification	Measurement Method		
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm		
	2.0	Primary Flat Orientation	{110} +/- 1 deg	Wafer Vendor	
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor	
	4.0	Secondary Flat Orientation	none	Wafer Vendor	
	5.0	Overall Thickness	525.00 +/- 5.00 μ m	ADE, 100%	
	6.0	Total Thickness Variation (TTV)	<5.00 μ m	Guaranteed by Process	
	7.0	Bow	<60.00 μ m	ADE to ASTM F534, 20%	
	8.0	Warp	<60.00 μ m	ADE to ASTM F657, 20%	
	9.0	Edge Chips	0	Bright Light, 100% (note 2)	
	10.0	Edge Exclusion	5mm		
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor	
	12.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor	
	12.1	Handle Carbon Concentration	< 1e15 at/cm3	Wafer Vendor	
	12.2	Handle Oxygen Concentration	< 1e18 at/cm3	Wafer Vendor	
	13.0	Handle Thickness	380.00 +/- 5.00 μ m	ADE, 100%	
	14.0	Handle Doping Type	N	Wafer Vendor	
	15.0	Handle Dopant	Arsenic	Wafer Vendor	
	16.0	Handle Resistivity	< 0.005 Ohm cm	Wafer Vendor	
17.0	Backside Finish	Lapped/etched w/ lasermark	Wafer Vendor		
DeviceSilicon	20.0	Device Growth Method	FZ	Wafer Vendor	
	21.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor	
	22.0	Nominal Thickness	145.00 +/- 5.00 μ m	FTIR, 100% 9-Pt (note3)	
	23.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process	
	24.0	Device Doping Type	N	Wafer Vendor	
	25.0	Device Dopant	Phosphorous	Wafer Vendor	
	26.0	Device Resistivity	2500 - 5500 Ohm-cm	Wafer Vendor	
	26.5	Buried Layer Implant	none	implant vendor	
	28.0	Voids	0	Bright Light, 100% (note 2)	
	29.0	Scratches	< 25mm total length	Bright Light, 100% (note 2)	
	30.0	Haze	none	Bright Light, 100% (note 2)	
	31.0	Device Field Oxidation	0.00 +/- 0.00		

Part Number	Customer	icemos tech ltd
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Category	Parameter	Specification	Measurement Method
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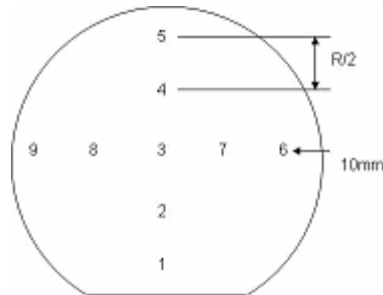
Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information